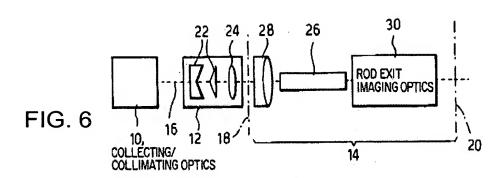


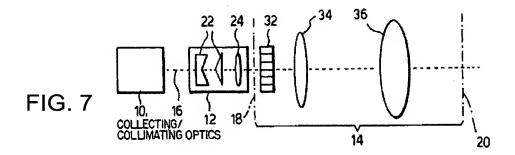
FIG. 2

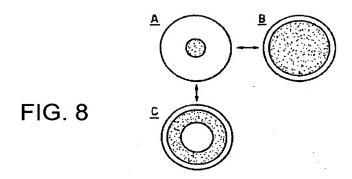
FIG. 3

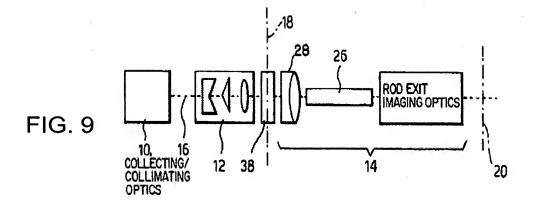
FIG. 4

FIG. 5









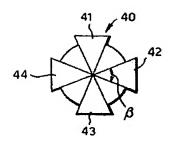


FIG. 10a

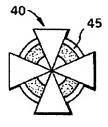


FIG. 10b

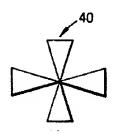


FIG. 11

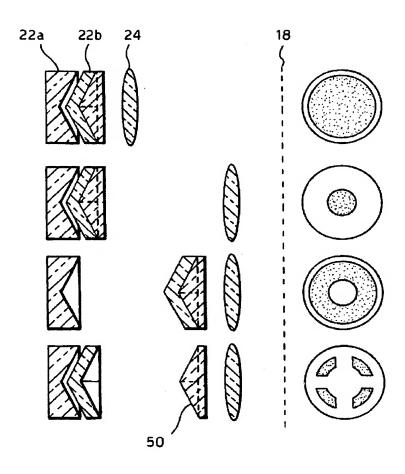


FIG. 12

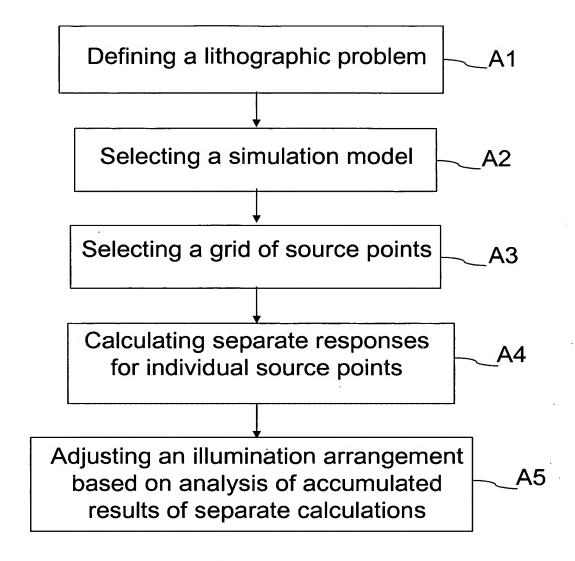
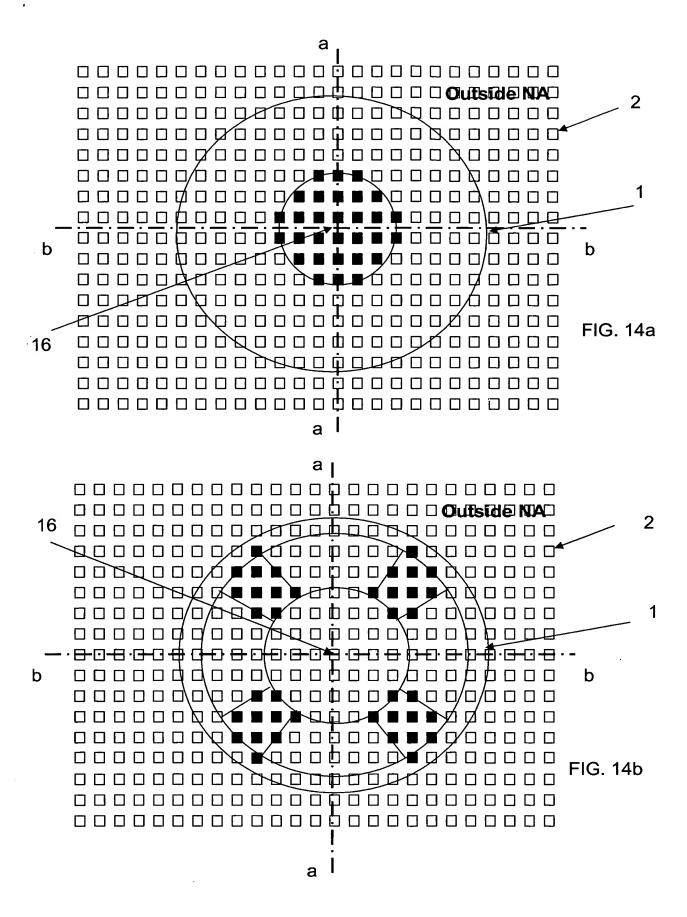


FIG. 13



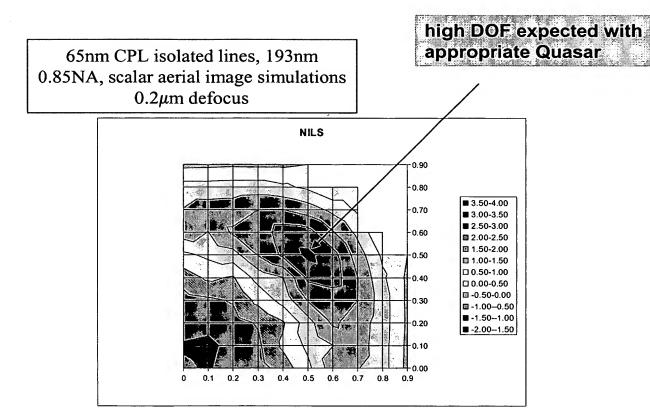


FIG. 15

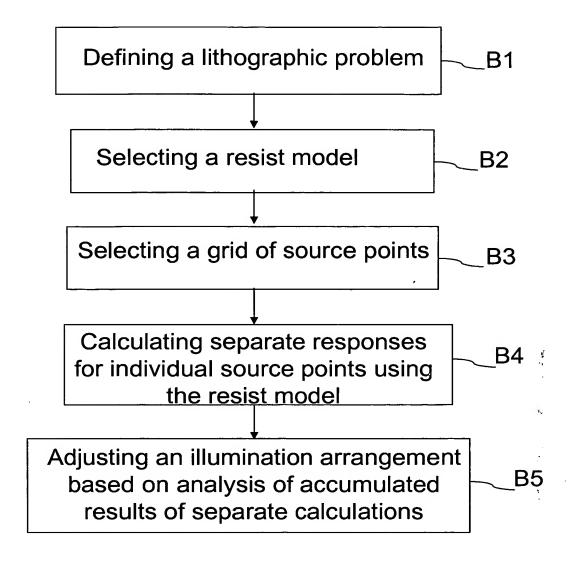


FIG. 16

# 65nm CPL isolated lines, 193nm 0.85NA, TOK63 vector resist simulations

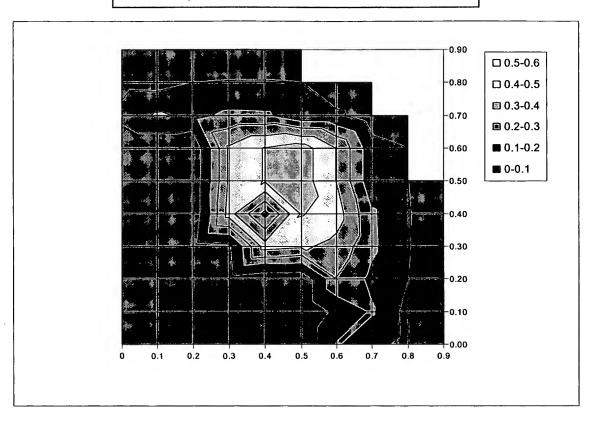


FIG. 17

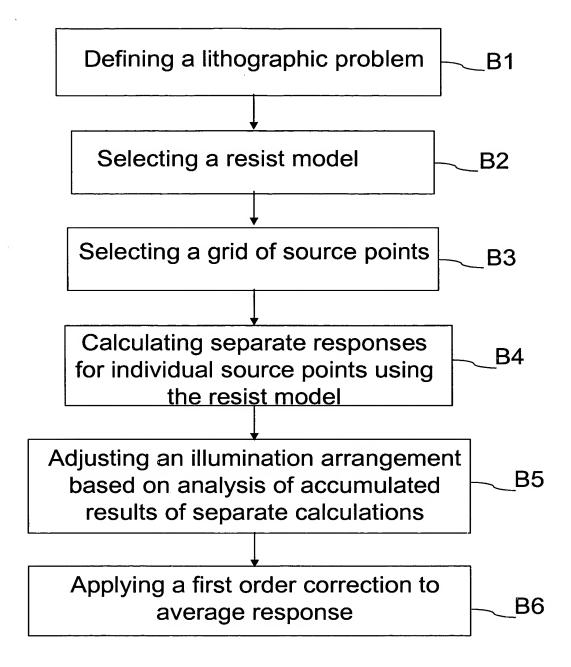


FIG. 18

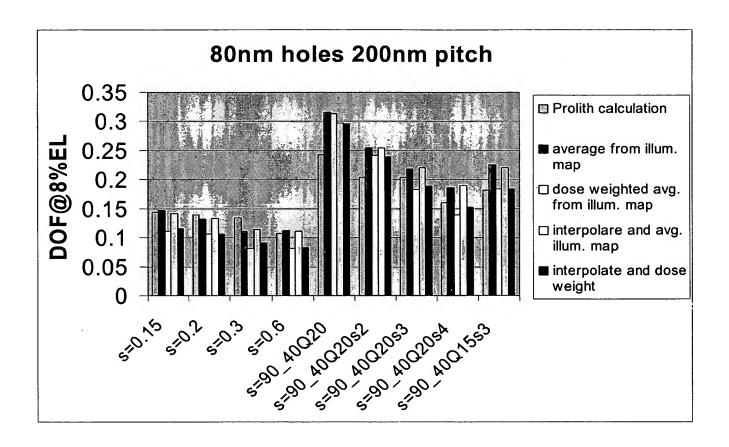
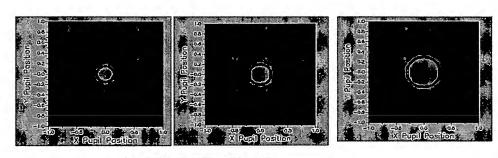
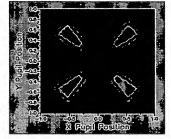


FIG. 19

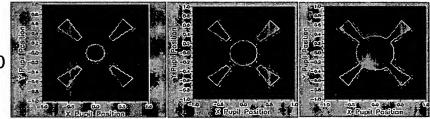
• 0.15, 0.2, 0.3, 0.6σ conv



• 0.9/0.4 Q20



• 0.2, 0.3, 0.4<sub>\sigma</sub> + 0.9/0.4 Q20



•  $0.3\sigma + 0.9/0.4 \text{ Q}15$ 

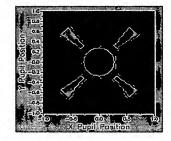


FIG. 20

trial illuminator	prediction based on weighted and interpolated source	Prolith simulation with this illuminator	
0.05.0.55000	measurements	0.00	
0.85_0.55Q30	0.293u	0.23u	
0.75 0.55Q20	0.416	0.41	
0.7 0_0.00 Q20	3.110	0.11	
0.80_0.60Q20	0.383	0.355	
_			
0.80_0.60annular	0.110	0.10	
0.75_0.55annular	0.118	0.105	

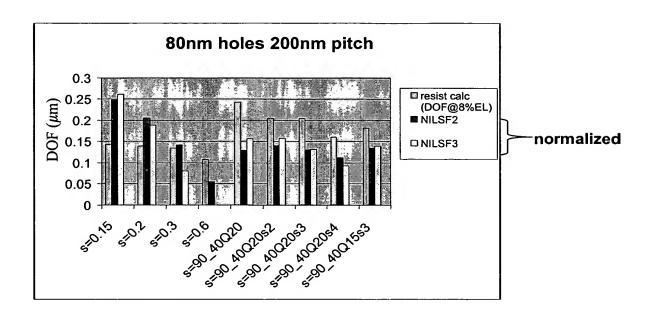


FIG. 22

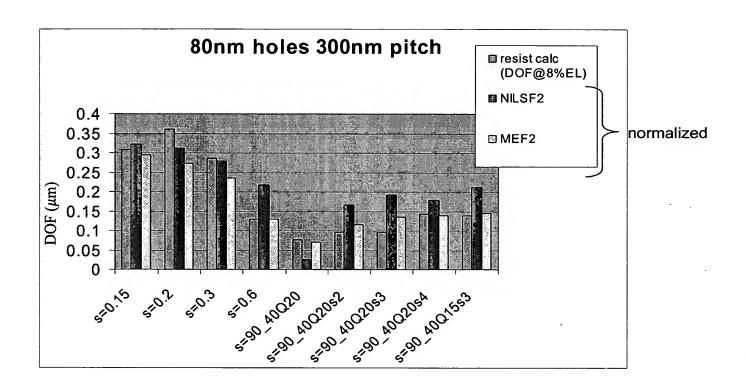


FIG. 23

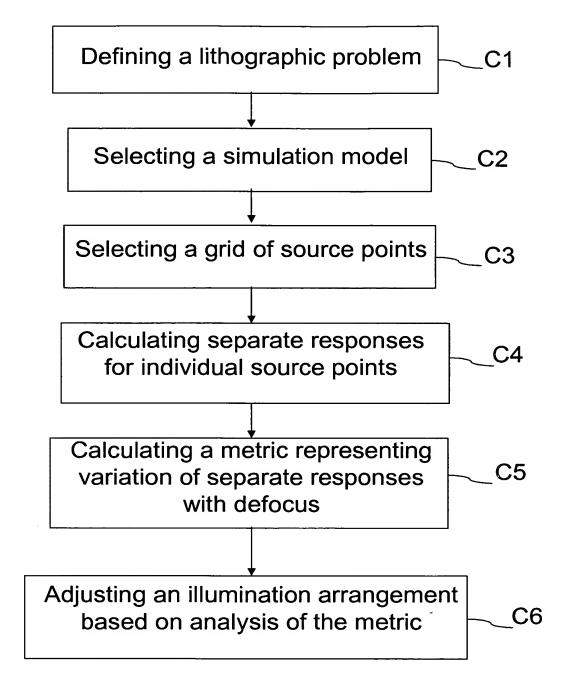
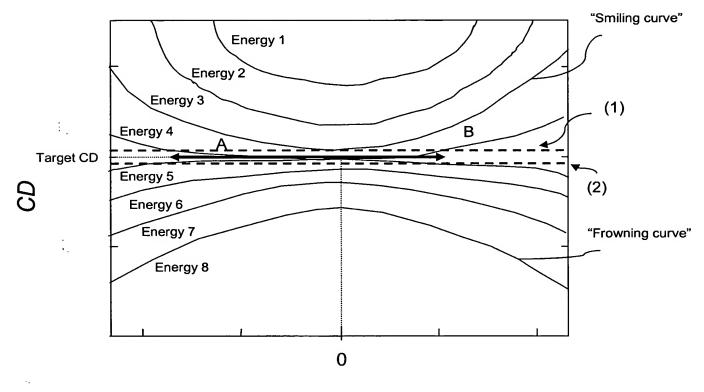
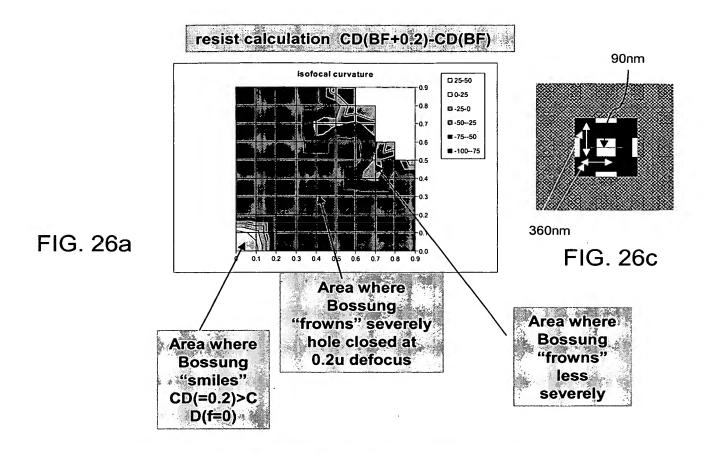


FIG. 24

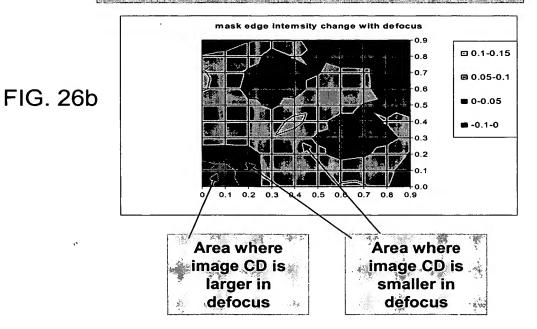


Focus

FIG. 25

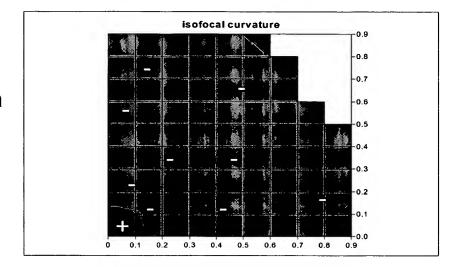


#### Aerial image calculation thresh(BF)-thresh(BF+0.2)



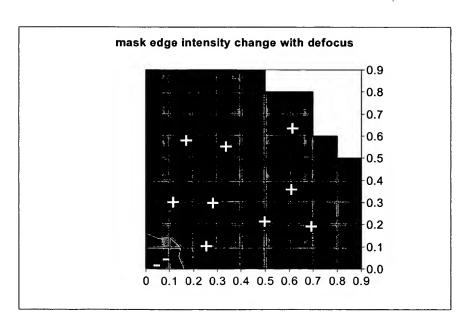
#### resist calculation CD(BF+0.2)-CD(BF)

FIG. 27a



Aerial image calculation thresh(BF)-thresh(BF+0.2)

FIG. 27b



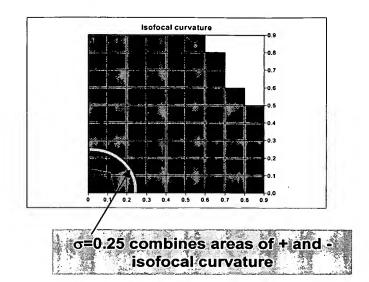
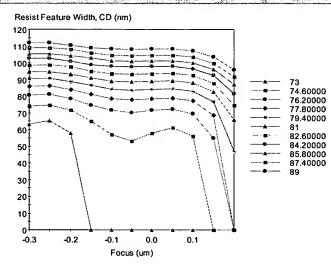
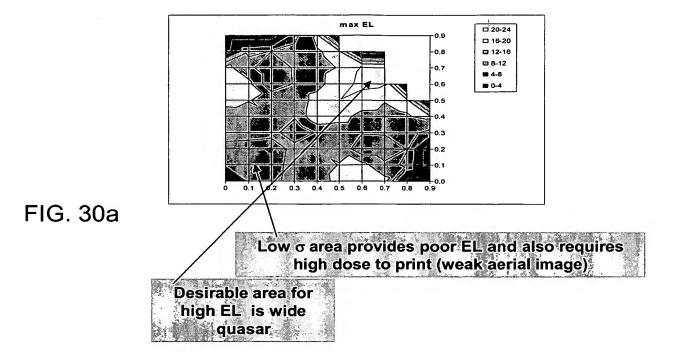


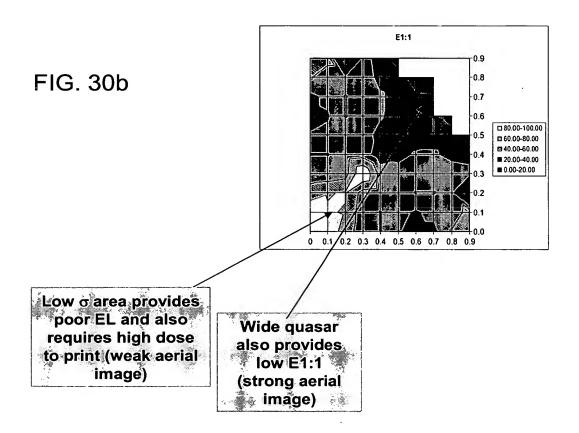
FIG. 28

At σ=0.25, process is approximately isofocal...
DOF is good but dose latitude is low.









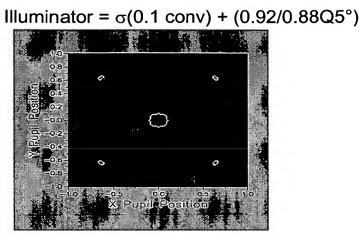
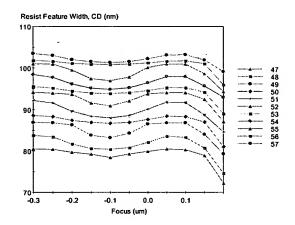


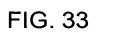
FIG. 31

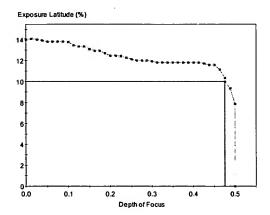
Custom #2

FIG. 32



Exposure Latitude vs. DOF





optimization method	illumination	max EL	max DOF	DOF @ 10% EL	DOF @ 5% EL
standard	0.95/0.70Q30°	18%	0.3	0.18	0.24
simple isofocal compensation	0.25 conv	8%	>0.55	0	0.29
high EL isofocal compensation	0.92/0.88Q5°+0.1conv	16%	>0.65	0.57	0.63

FIG. 34

Large
improvement in
process window
may be possible
by appropriate
use of illuminator
to compensate
isofocal curvature

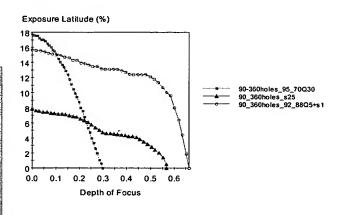
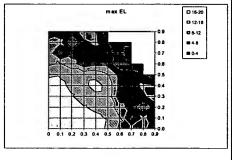


FIG. 35a



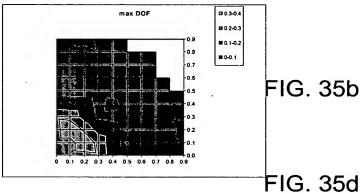
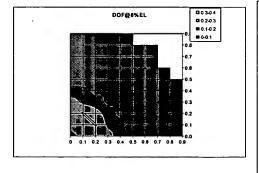
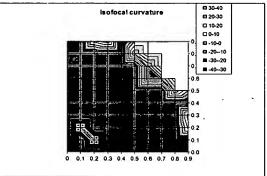


FIG. 35c





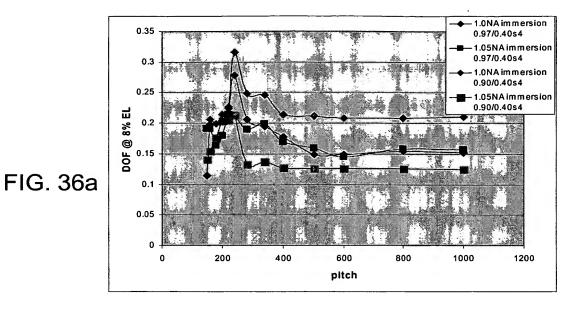
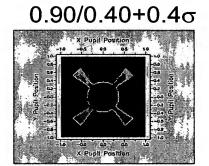


FIG. 36b



0.97/0.40+0.4σ

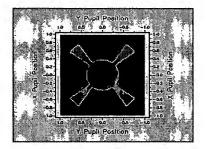


FIG. 36c

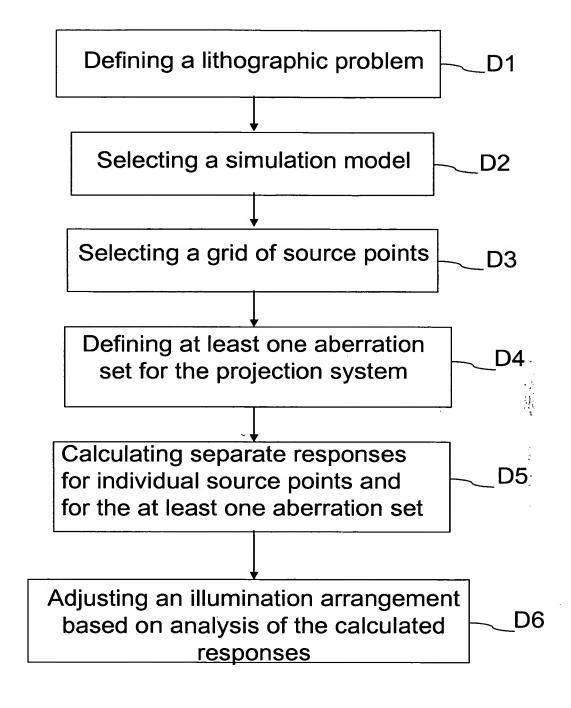
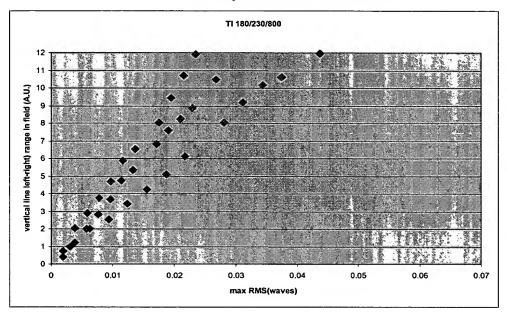


FIG. 37

# Under these conditions, the structure is very aberration sensitive



double line
line
PSW
180 phase
shift window

FIG. 38a

FIG. 38b

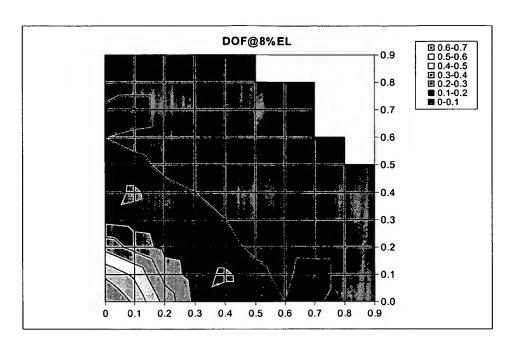


FIG. 39a

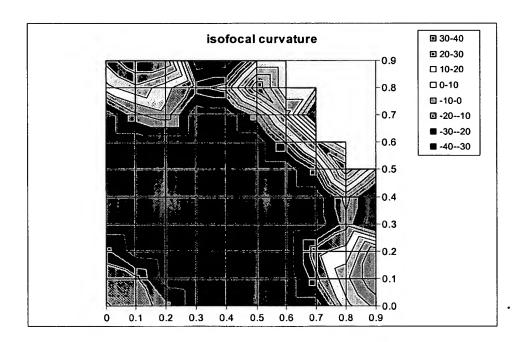
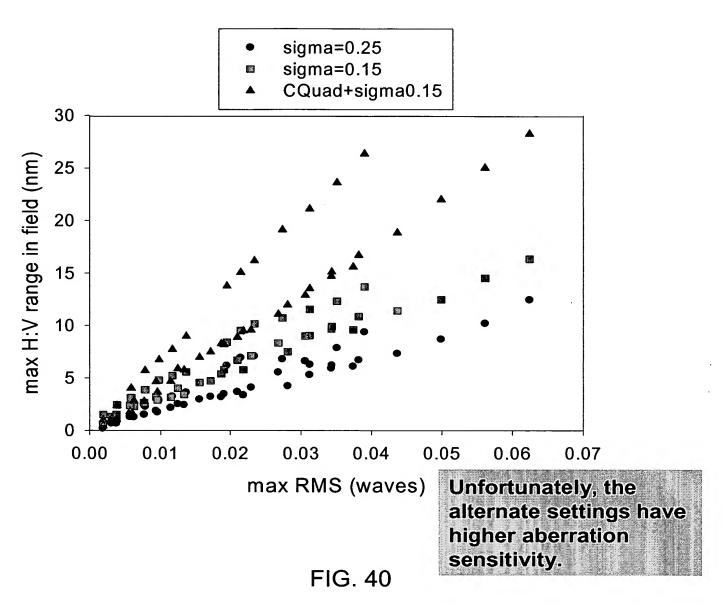
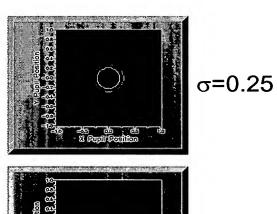
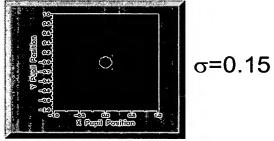


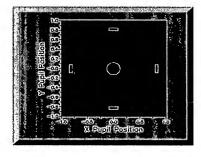
FIG. 39b

## Illuminator comparison for double line









σ=0.15 + small Cquad

FIG. 41

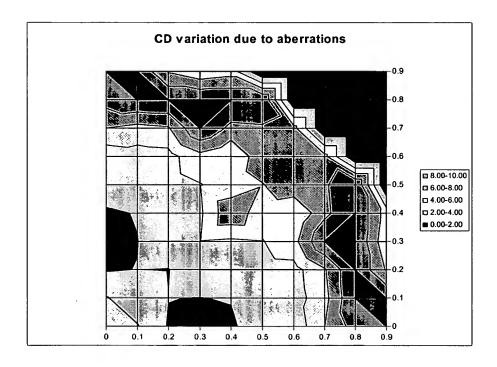
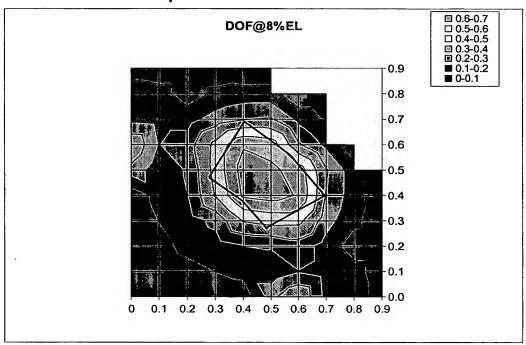


FIG. 42

# Illum. Optimization with 0.75NA



tight Quasar looks best ⇒ 0.80/0.55Q30°

FIG. 43

## Source visualization of aberration sensitivity

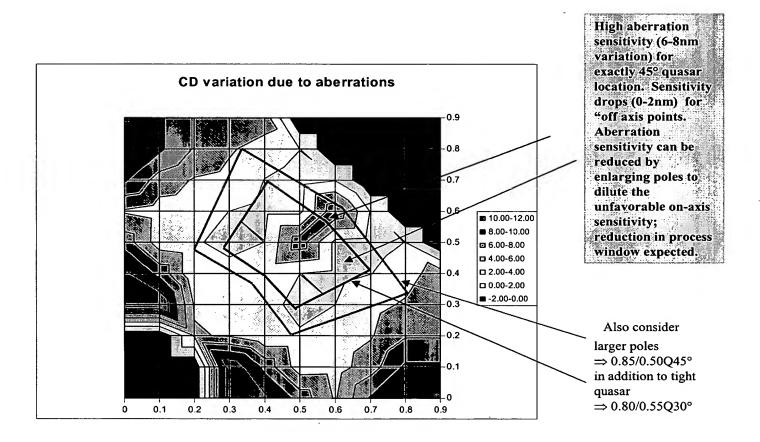


FIG. 44

# Illuminator comparison for double line

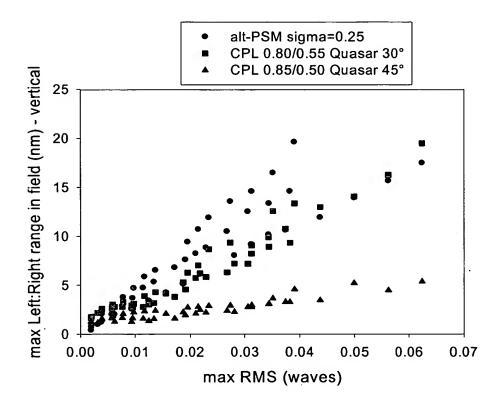


FIG. 45

# CPL with reduced aberration sensitivity increased pole size still gives favorable process window

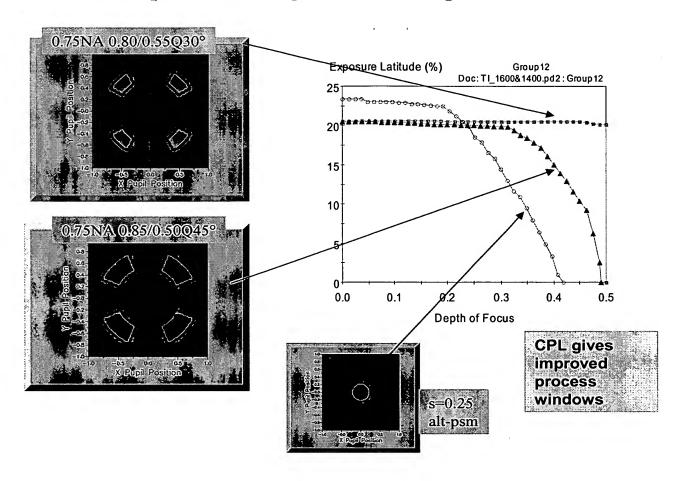


FIG. 46

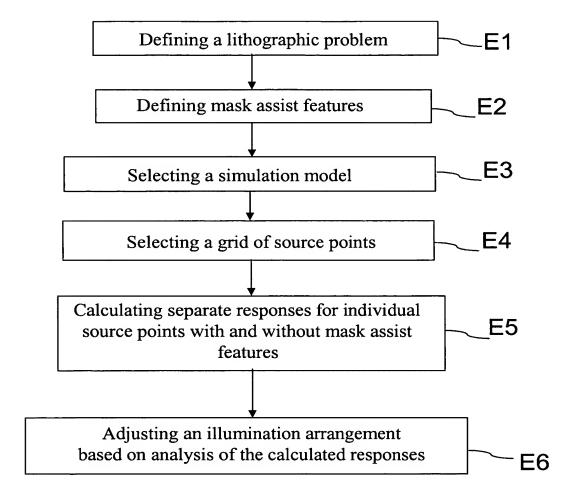


FIG. 47

# 6%Att-PSM, 1Anti-Scatterring Bar (ASB)/side 50nm ASB, 150nm pitch

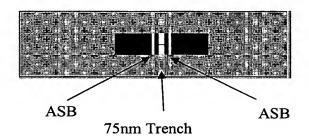
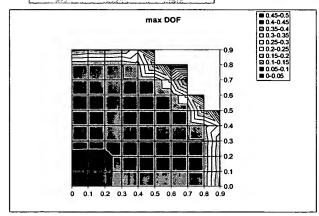


FIG. 48

#### Optimization requires very wide CQuad or quasar

#### 75nm trench, 15nm bias 6% att-psm,193nm 0.93NA



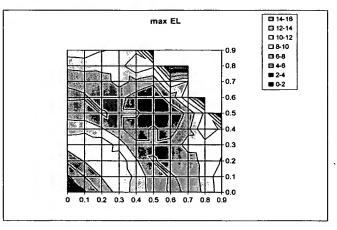


FIG. 49a

FIG. 49b

#### 75nm trench, 15nm bias 6% att-psm, 193nm 0.93NA

### 1SB / side



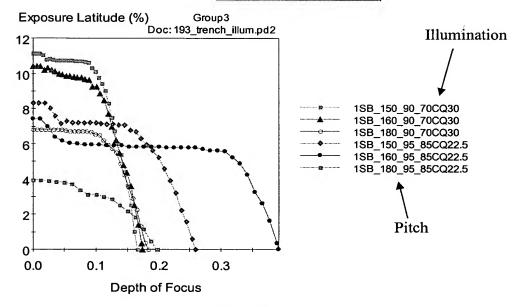
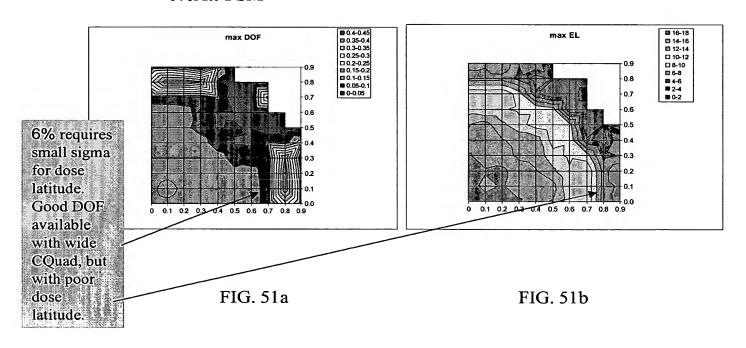
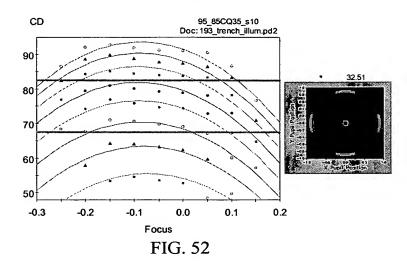


FIG. 50

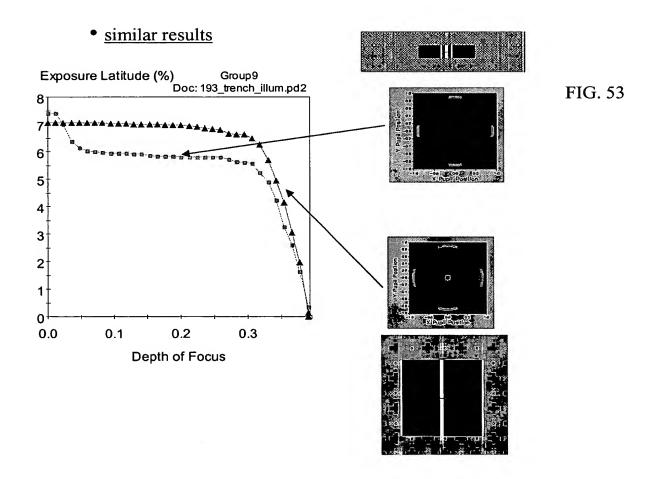
#### 6%Att-PSM



#### $35^{\circ}$ Cquad + $0.10\sigma$



### Comparison of "mask assist" and "illuminator assist" for high DOF

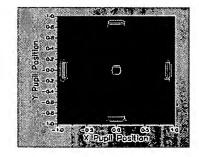


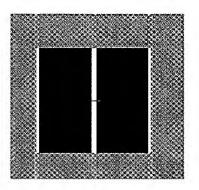
#### Effect of bias

• Lower bias increases DOF. This is an advantage for the "simple mask, complex illuminator" case because there are no assist features to print when using low biases / high exposures.

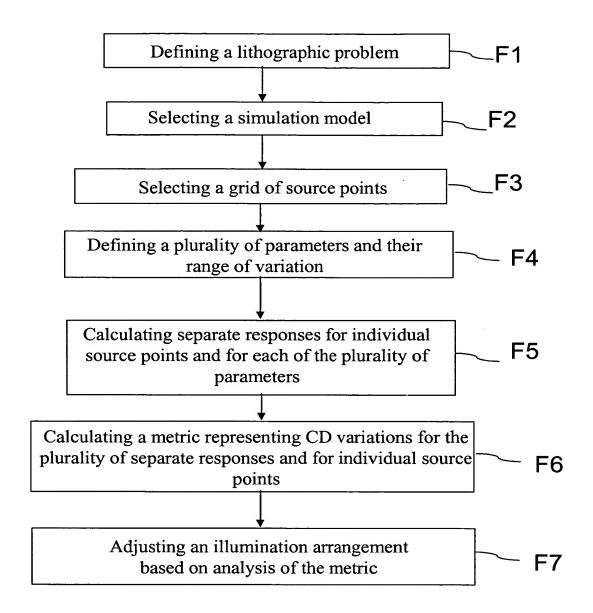
Exposure Latitude (%) Group5 Doc: 193\_trench\_illum.pd2 10 -5nm 6 25nm 4 95\_85CQ22.5\_s10\_15b 95\_85CQ22.5\_s10\_25b 2 95\_85\_CQ22.5\_s10\_-5b 0 0.0 0.1 0.2 0.3 0.4 **Depth of Focus** 

75nm trench, variable bias 6% att-psm, 193nm 0.93NA





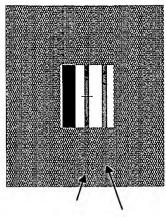
**FIG.54** 



t, a

FIG. 55

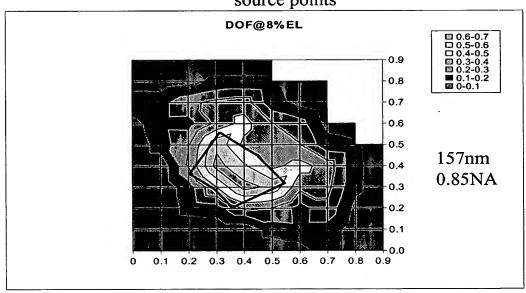
#### CPL for double line



Print 50nm lines

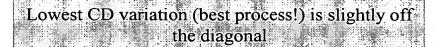
FIG. 56

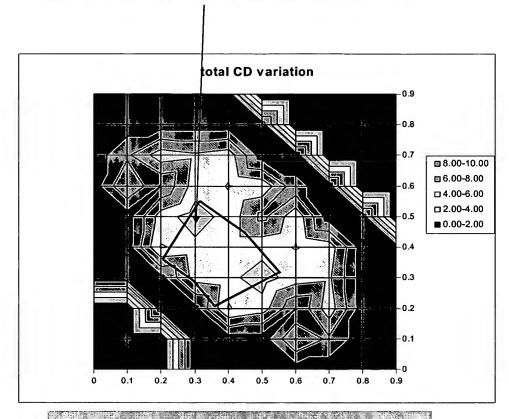
#### Source visualization map based on resist simulations for a grid of source points



"Best choice" for illumination based on process window metric is the indicated 0.64/0.42Quasar30°.

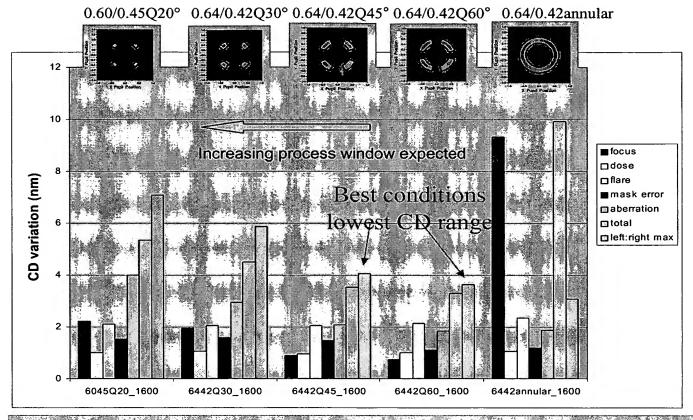
Note: smaller poles centered at the same location expected to give better process window - larger worse.





Expect wider pole to improved CDU

FIG. 58



Selecting illuminator based on process window alone gives >50% more CD variation than if source visualization of CDU is included

FIG. 59